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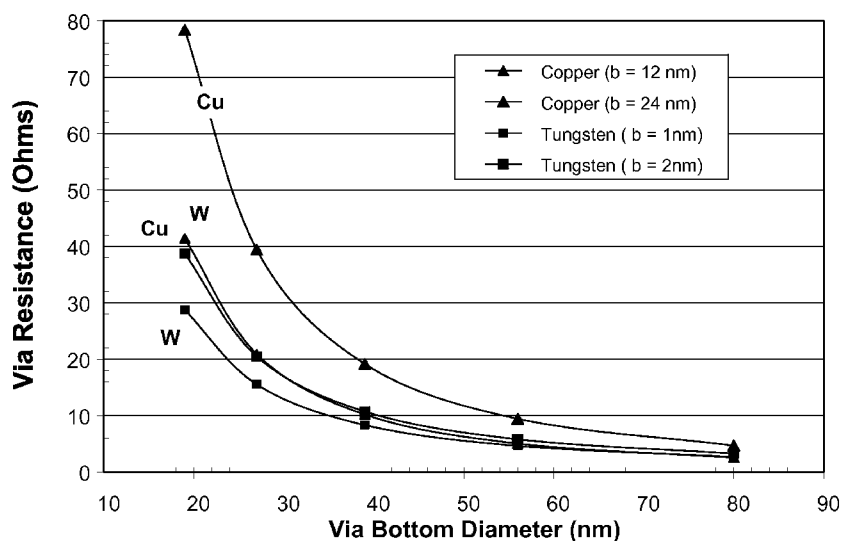
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(54) Title: SUBTRACTIVE PATTERNING TO DEFINE CIRCUIT COMPONENTS

**Figure 7**

(57) Abstract: Certain embodiments pertain to local interconnects formed by subtractive patterning of blanket layer of tungsten or other conductive material. The grain sizes of tungsten or other deposited metal can be grown to relatively large dimensions, which results in increased electrical conductivity due to, e.g., reduced electron scattering at grain boundaries as electrons travel from one grain to the next during conduction.